

## 2SK2735(L), 2SK2735(S)

Silicon N Channel MOS FET  
High Speed Power Switching

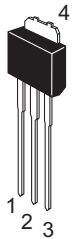
REJ03G1029-0200  
(Previous: ADE-208-543)  
Rev.2.00  
Sep 07, 2005

### Features

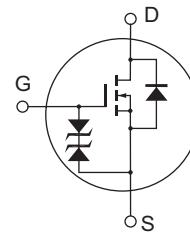
- Low on-resistance  
 $R_{DS} = 20 \text{ m}\Omega$  typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

### Outline

RENESAS Package code: PRSS0004ZD-B  
(Package name: DPAK(L)-(2))



RENESAS Package code: PRSS0004ZD-C  
(Package name: DPAK(S))



1. Gate
2. Drain
3. Source
4. Drain

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	30	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	20	A
Drain peak current	$I_{D(pulse)}^{*1}$	80	A
Body to drain diode reverse drain current	$I_{DR}$	20	A
Channel dissipation	$P_{ch}^{*2}$	20	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1 \%$   
 2. Value at  $T_c = 25^\circ C$

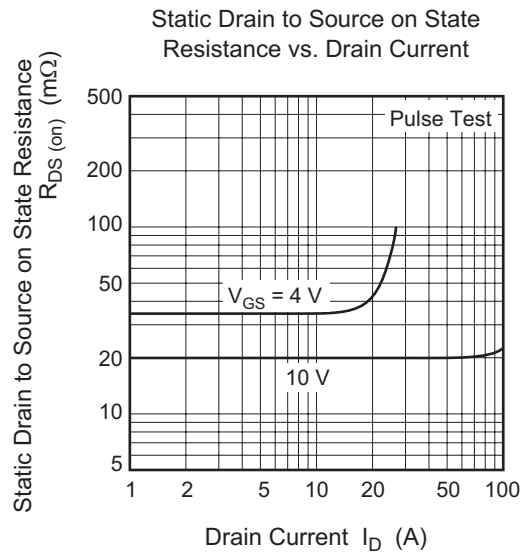
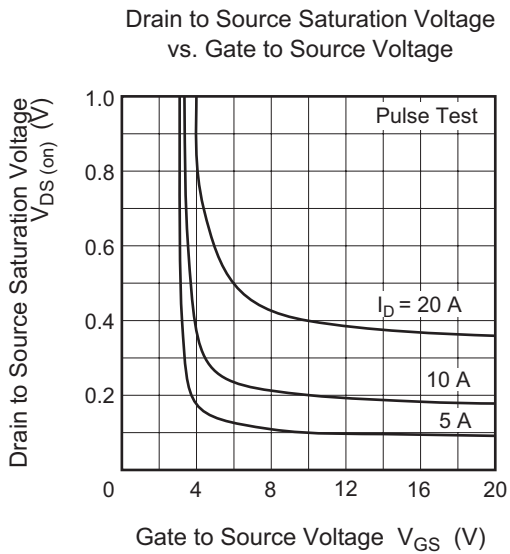
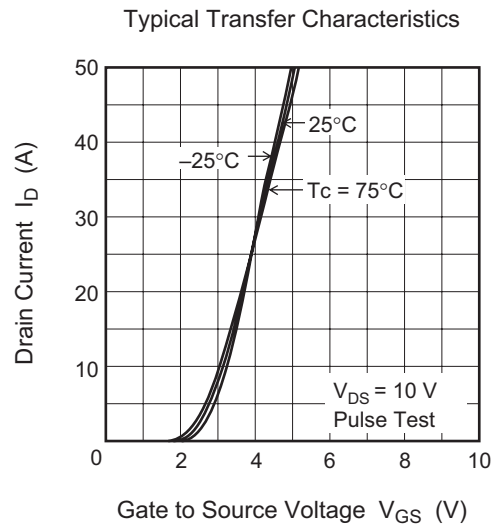
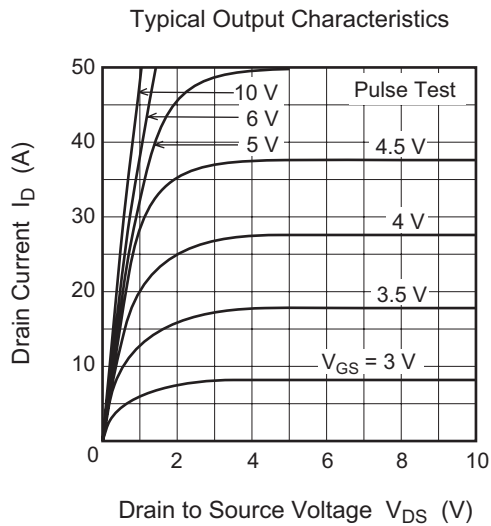
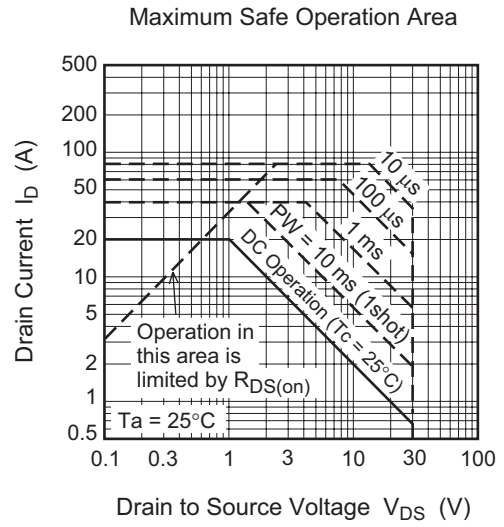
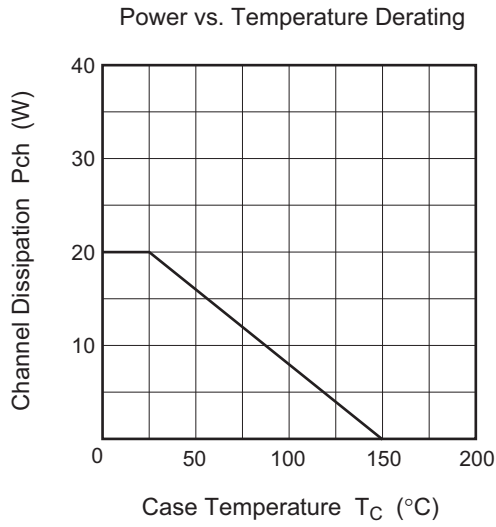
## Electrical Characteristics

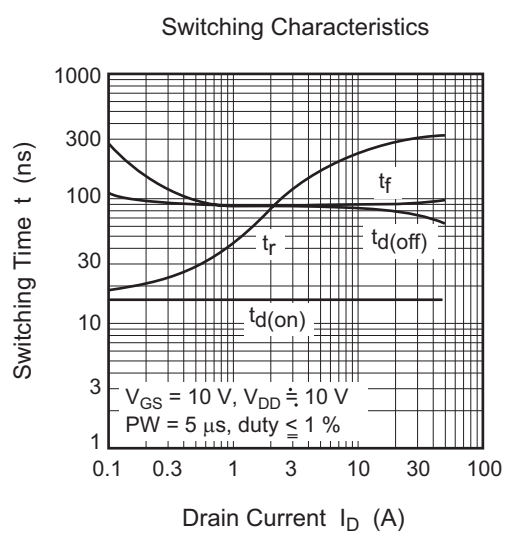
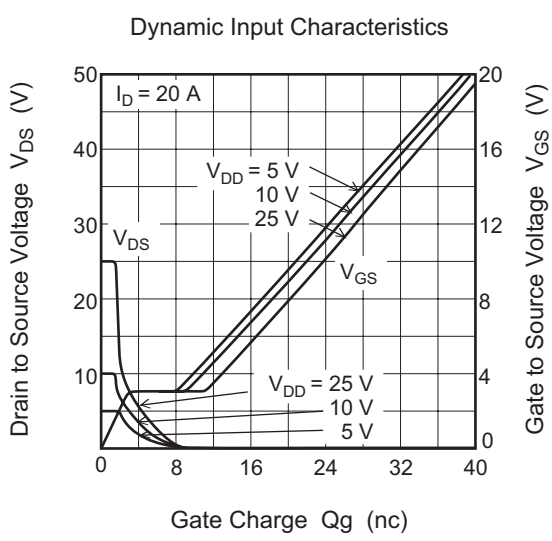
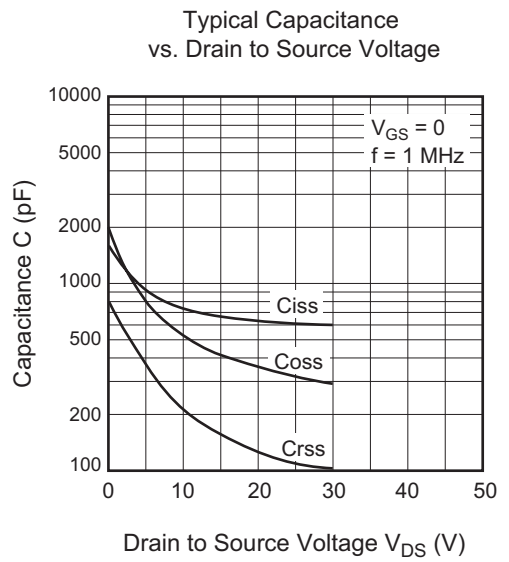
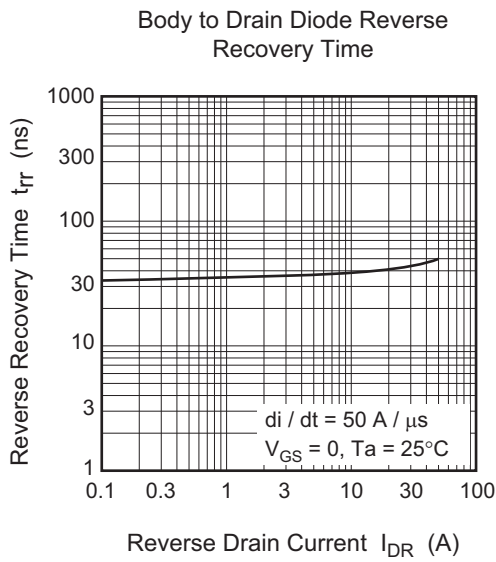
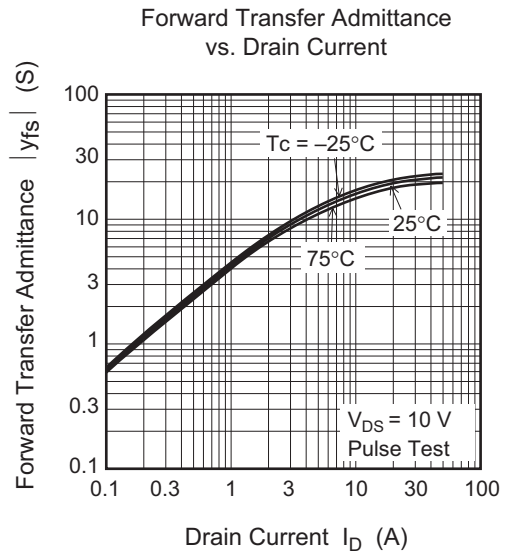
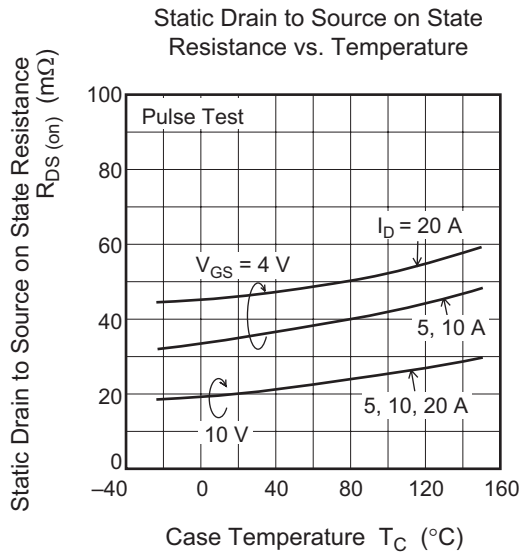
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	10	μA	$V_{DS} = 30 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 \text{ mA}$ , $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	20	28	mΩ	$I_D = 10 \text{ A}$ , $V_{GS} = 10 \text{ V}^{*3}$
	$R_{DS(on)}$	—	35	50	mΩ	$I_D = 10 \text{ A}$ , $V_{GS} = 4 \text{ V}^{*3}$
Forward transfer admittance	$ y_{fs} $	8	16	—	S	$I_D = 10 \text{ A}$ , $V_{DS} = 10 \text{ V}^{*3}$
Input capacitance	$C_{iss}$	—	750	—	pF	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	520	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	210	—	pF	
Turn-on delay time	$t_{d(on)}$	—	16	—	ns	$I_D = 10 \text{ A}$ , $V_{GS} = 10 \text{ V}$ , $R_L = 1 \Omega$
Rise time	$t_r$	—	225	—	ns	
Turn-off delay time	$t_{d(off)}$	—	85	—	ns	
Fall time	$t_f$	—	90	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	1.0	—	V	$I_F = 20 \text{ A}$ , $V_{GS} = 0$ $di_F/dt = 50 \text{ A}/\mu s$
Body to drain diode reverse recovery time	$t_{rr}$	—	40	—	V	$I_F = 20 \text{ A}$ , $V_{GS} = 0$ $di_F/dt = 50 \text{ A}/\mu s$

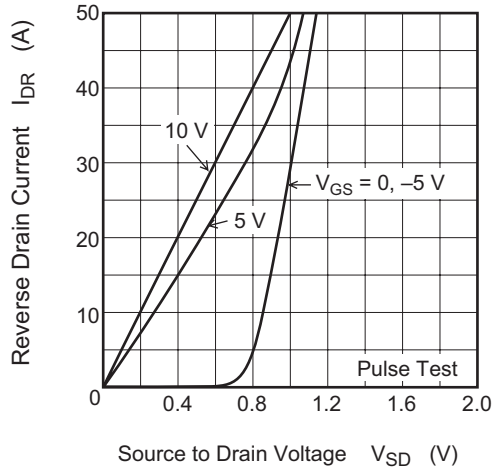
Note: 3. Pulse test

Main Characteristics

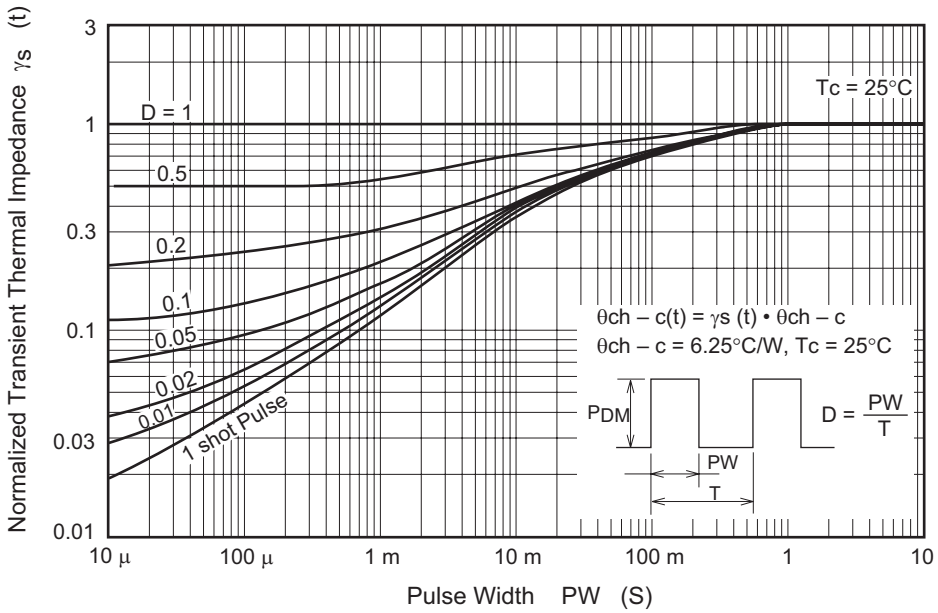




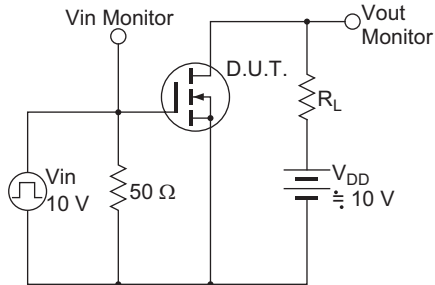
Reverse Drain Current vs. Source to Drain Voltage



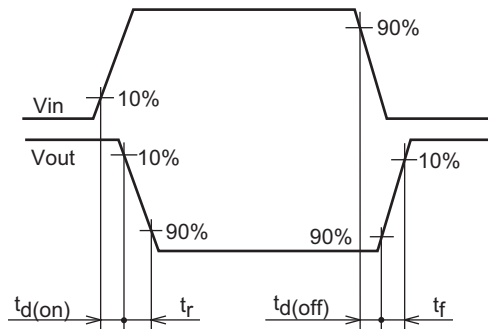
Normalized Transient Thermal Impedance vs. Pulse Width



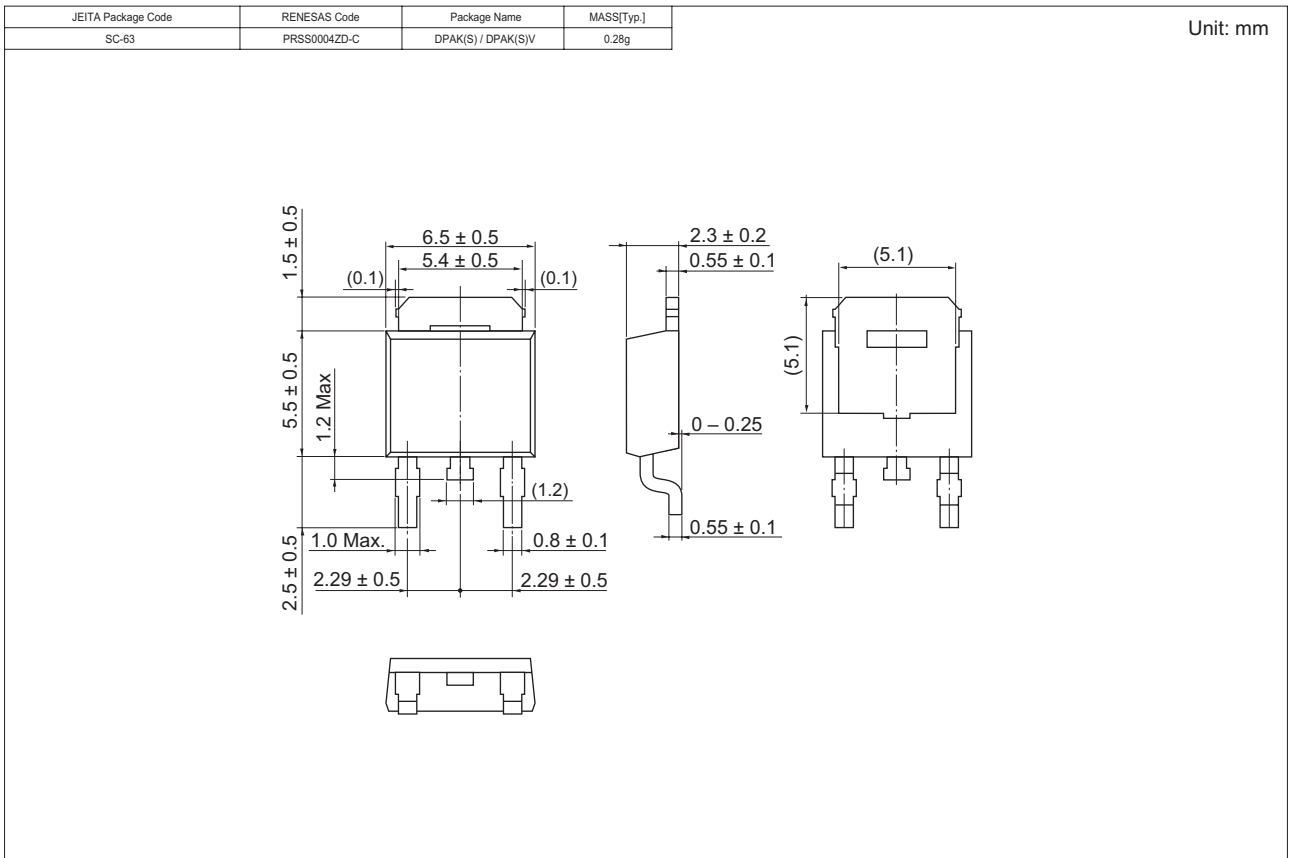
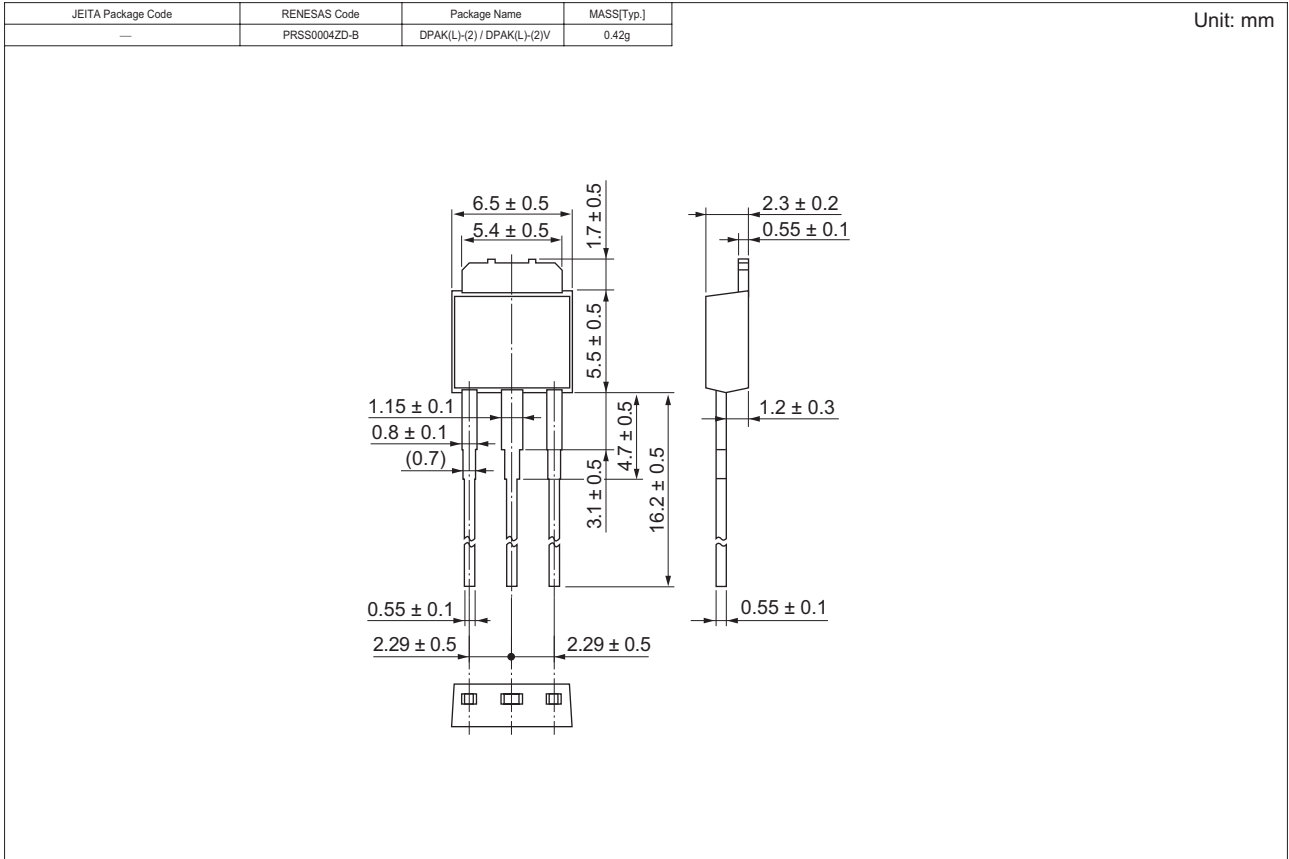
Switching Time Test Circuit



Waveform



Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
2SK2735L-E	3200 pcs	Box (Sack)
2SK2735STL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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